SamHop Microelectronics Corp.

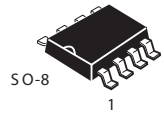
STM8450

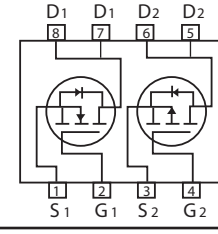
Nov.23, 2004 ver1.3

Dual Enhancement Mode Field Effect Transistor (N and P Channel)

PRODUCT SUMMARY (N-Channel)		
V_{DSS}	I_D	$R_{DS(ON)}$ (mΩ) Max
40V	5A	35 @ V_{GS} = 10V
		60 @ V_{GS} = 4.5V

PRODUCT SUMMARY (P-Channel)		
V_{DSS}	I_D	$R_{DS(ON)}$ (mΩ) Max
-40V	-4A	45 @ V_{GS} = -10V
		60 @ V_{GS} = -4.5V





ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Parameter		Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage		V_{DS}	40	-40	V
Gate-Source Voltage		V_{GS}	±20	±20	V
Drain Current-Continuous [a] @ Ta	25°C	I_D	5	-4	A
	70°C		4.2	-3.4	A
-Pulsed [b]		I_{DM}	20	-16	A
Drain-Source Diode Forward Current [a]		I_S	1.7	-1.7	A
Maximum Power Dissipation [a]	Ta= 25°C	P_D	2		W
	Ta=70°C		1.44		
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150		°C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient [a]	$R_{\theta JA}$	62.5	°C/W

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N-Channel ELECTRICAL CHARACTERISTICS (T_A = 25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ [c]	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} =0V, I_D=250uA	40			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} =32V, V_{GS}=0V			1	uA
Gate-Body Leakage	I_{GSS}	V_{GS} =±20V, V_{DS}= 0V			±100	nA
ON CHARACTERISTICS [b]						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D = 250uA	1.0	2.0	3.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS} =10V, I_D =5A		25	35	m ohm
		V_{GS} =4.5V, I_D= 4A		50	60	m ohm
On-State Drain Current	$I_{D(ON)}$	V_{DS} = 5V, V_{GS} = 10V	15			A
Forward Transconductance	g_{FS}	V_{DS} = 5V, I_D = 5A		8		S
DYNAMIC CHARACTERISTICS [c]						
Input Capacitance	C_{ISS}	V_{DS} =10V, V_{GS} = 0V f =1.0MHz		910	995	pF
Output Capacitance	C_{OSS}			130	150	pF
Reverse Transfer Capacitance	C_{RSS}			95	108	pF
Gate resistance	Rg	V_{GS} =0V, V_{DS} = 0V, f=1.0MHz		3		ohm
SWITCHING CHARACTERISTICS [c]						
Turn-On Delay Time	$t_{D(ON)}$	V_{DD} = 15V I_D = 3 A V_{GS} = 10V R_{GEN} = 4.7 ohm		17	19	ns
Rise Time	t_r			4.3	5	ns
Turn-Off Delay Time	$t_{D(OFF)}$			23.5	27	ns
Fall Time	t_f			9.5	11	ns
Total Gate Charge	Q_g	V_{DS} =24V, I_D =5A,V_{GS} =10V		18.3	21	nC
		V_{DS} =24V, I_D =5A,V_{GS} =4.5V		9	10	nC
Gate-Source Charge	Q_{gs}	V_{DS} =24V, I_D = 5 A V_{GS} =4.5V		3.3	4	nC
Gate-Drain Charge	Q_{gd}			4.2	5	nC

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P-Channel ELECTRICAL CHARACTERISTICS (T_A = 25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ [c]	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} =0V, I_D =-250uA	-40			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} =-32V, V_{GS}= 0V			-1	uA
Gate-Body Leakage	I_{GSS}	V_{GS} =±20V, V_{DS}= 0V			±100	nA
ON CHARACTERISTICS [b]						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D = -250uA	-0.8	-1.5	-2.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS} =-10V, I_D= -4A		35	45	m ohm
		V_{GS} =-4.5V, I_D= -3A		50	60	m ohm
On-State Drain Current	$I_{D(ON)}$	V_{DS} = -5V, V_{GS} = -10V	20			A
Forward Transconductance	g_{FS}	V_{DS} = -5V, I_D= -4A		8		S
DYNAMIC CHARACTERISTICS [c]						
Input Capacitance	C_{ISS}	V_{DS} =-10V, V_{GS} = 0V f =1.0MHz		1128	1250	pF
Output Capacitance	C_{OSS}			182	210	pF
Reverse Transfer Capacitance	C_{RSS}			110	130	pF
Gate resistance	Rg	V_{GS} =0V, V_{DS} = 0V, f=1.0MHz		3.5		ohm
SWITCHING CHARACTERISTICS [c]						
Turn-On Delay Time	$t_{D(ON)}$	V_{DD} = -15V I_D= -2.2A V_{GS} = -10V R_{GEN} = 4.7 ohm		17.3	20	ns
Rise Time	t_r			7	8	ns
Turn-Off Delay Time	$t_{D(OFF)}$			82	95	ns
Fall Time	t_f			27.6	32	ns
Total Gate Charge	Q_g	V_{DS} =-24V, I_D =-4A,V_{GS} =-10V		20.5	23	nC
		V_{DS} =-24V, I_D =-4A,V_{GS} =-4.5V		9.8	11	nC
Gate-Source Charge	Q_{gs}	V_{DS} =-24V, I_D = -4 A V_{GS} =-4.5V		2.8	3.2	nC
Gate-Drain Charge	Q_{gd}			3.9	4.5	nC

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition		Min	Typ [c]	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS [b]							
Diode Forward Voltage	V_{SD}	V_{GS} = 0V, Is =1.7A	N-Ch		0.8	1.2	V
		V_{GS} = 0V, Is =-1.7A	P-Ch		-0.77	-1.2	

Notes

a.Surface Mounted on FR4 Board, t≤10sec.
b.Pulse Test:Pulse Width≤300 μs, Duty Cycle≤2%.
c.Guaranteed by design, not subject to production testing.
N-Channel

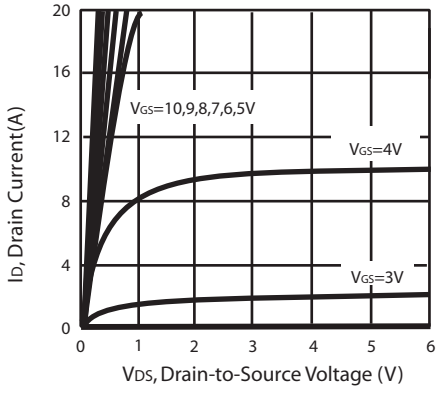

Figure 1. Output Characteristics

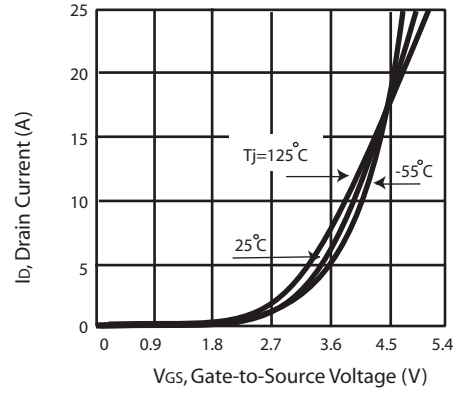

Figure 2. Transfer Characteristics

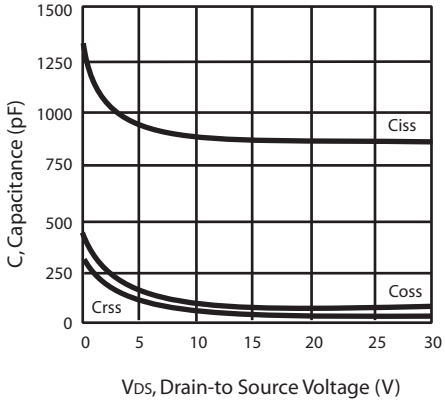

Figure 3. Capacitance

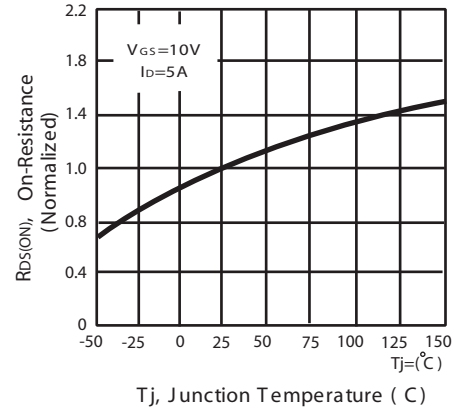

Figure 4. On-Resistance Variation with Drain Current and Temperature

N-Channel

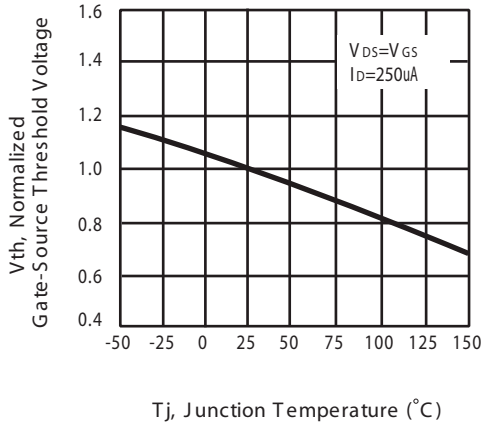

Figure 5. Gate Threshold Variation with Temperature

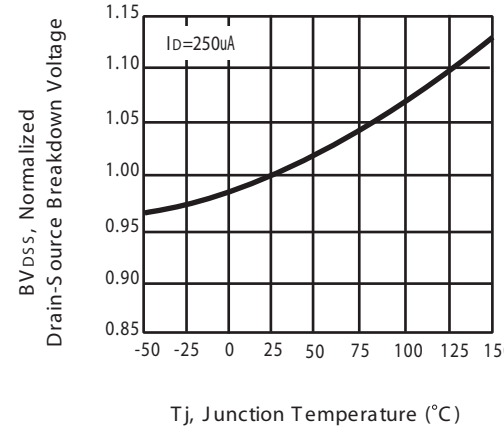

Figure 6. Breakdown Voltage Variation with Temperature

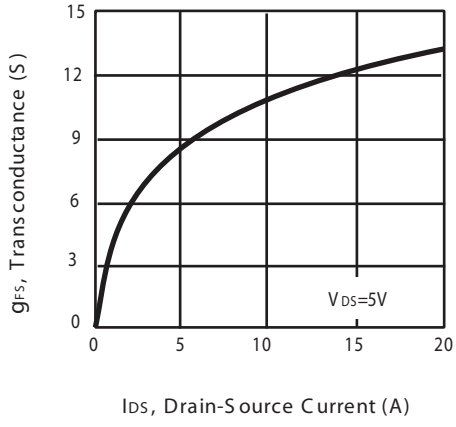

Figure 7. Transconductance Variation with Drain Current

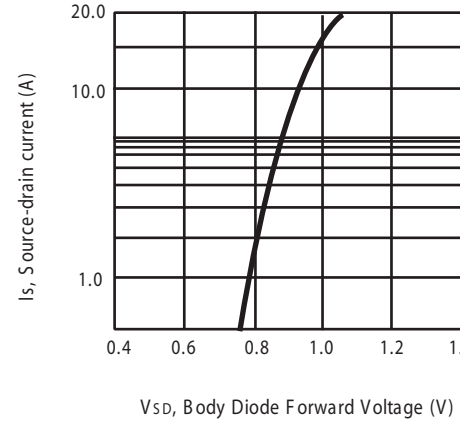

Figure 8. Body Diode Forward Voltage Variation with Source Current

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P-Channel

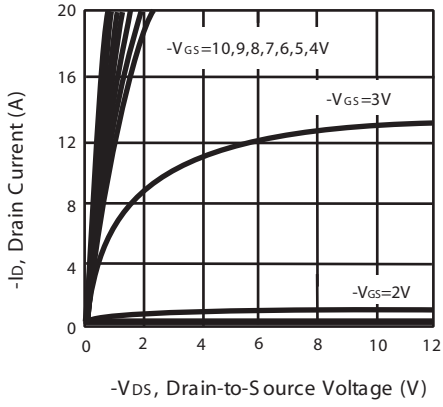

Figure 1. Output Characteristics

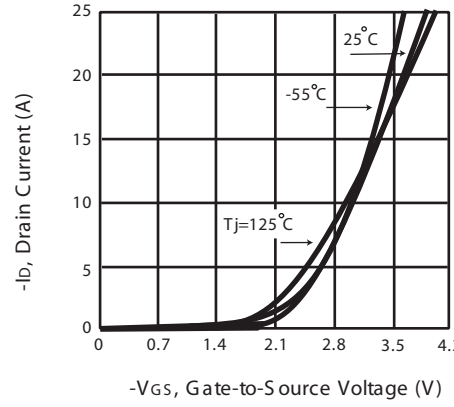

Figure 2. Transfer Characteristics

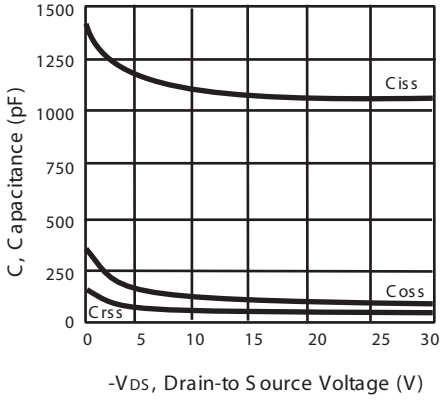

Figure 3. Capacitance

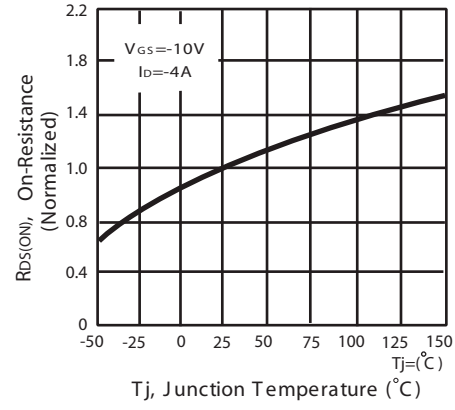

Figure 4. On-Resistance Variation with Temperature

P-Channel

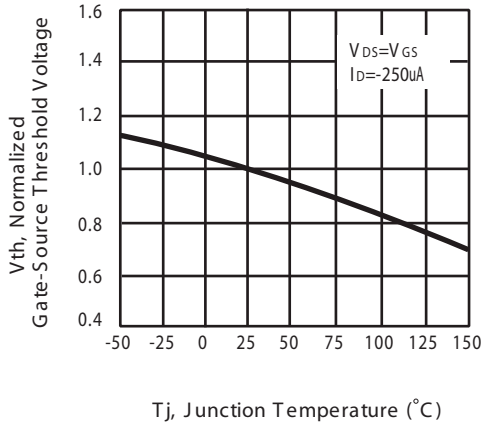

Figure 5. Gate Threshold Variation with Temperature

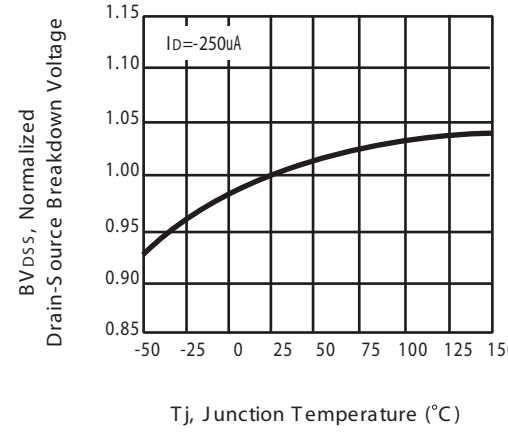

Figure 6. Breakdown Voltage Variation with Temperature

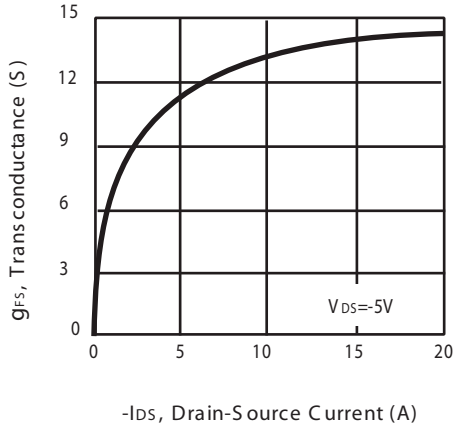

Figure 7. Transconductance Variation with Drain Current

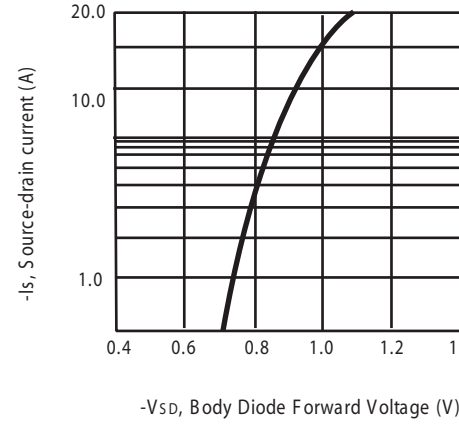

Figure 8. Body Diode Forward Voltage Variation with Source Current

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N-Channel

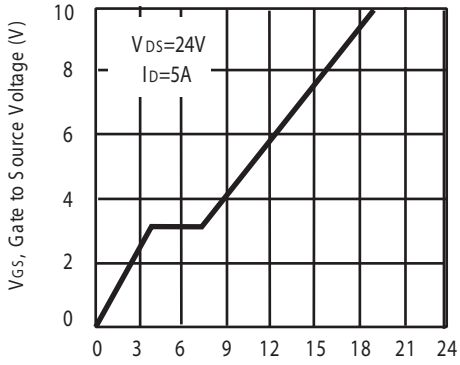


Figure 9. Gate Charge

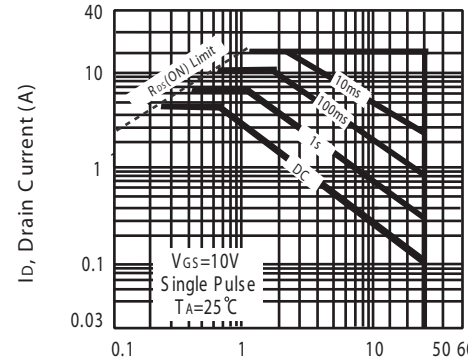
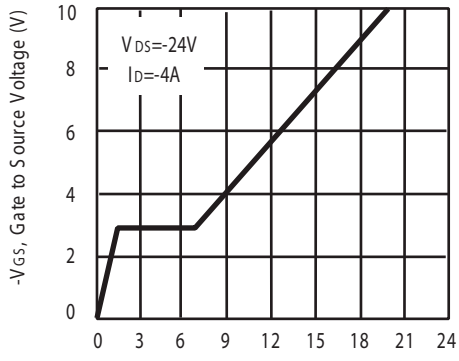


Figure 10. Maximum Safe Operating Area

P-Channel



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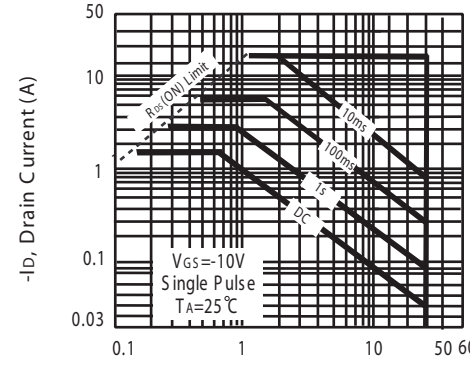

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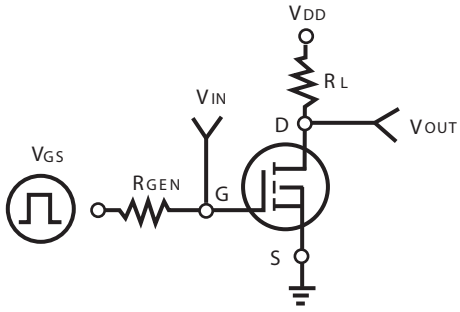


Figure 11. Switching Test Circuit

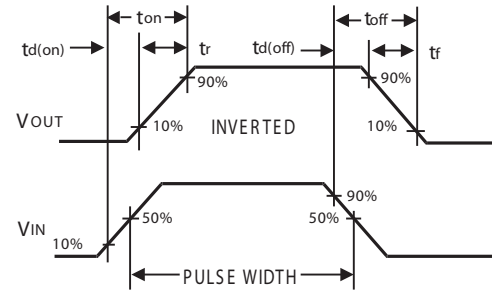
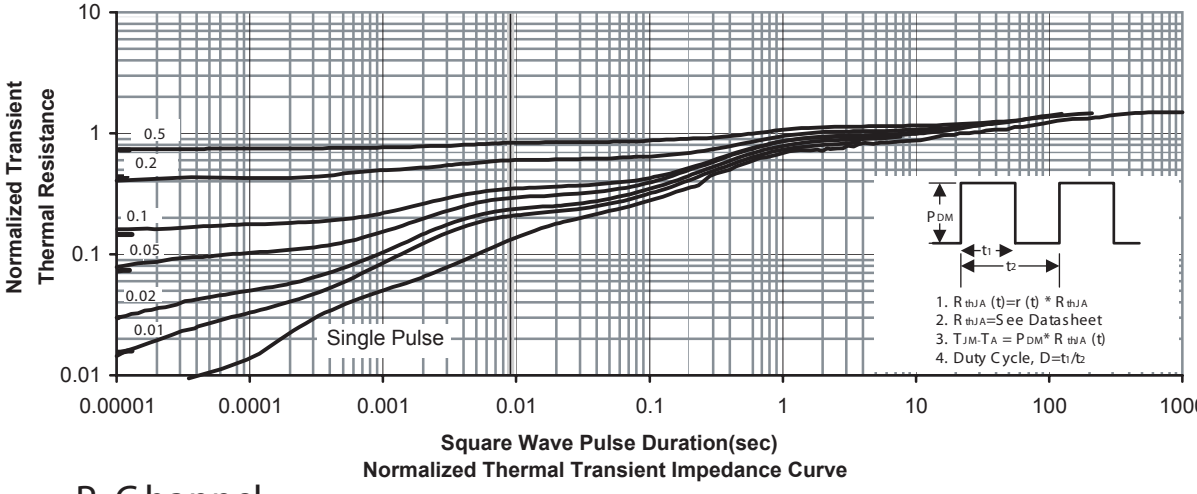
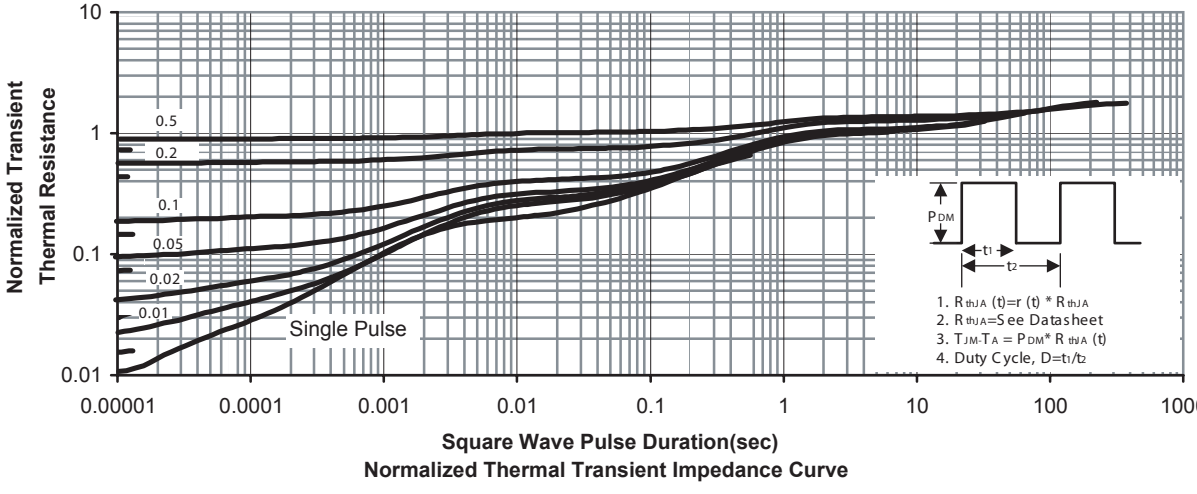


Figure 12. Switching Waveforms

N-Channel



P-Channel



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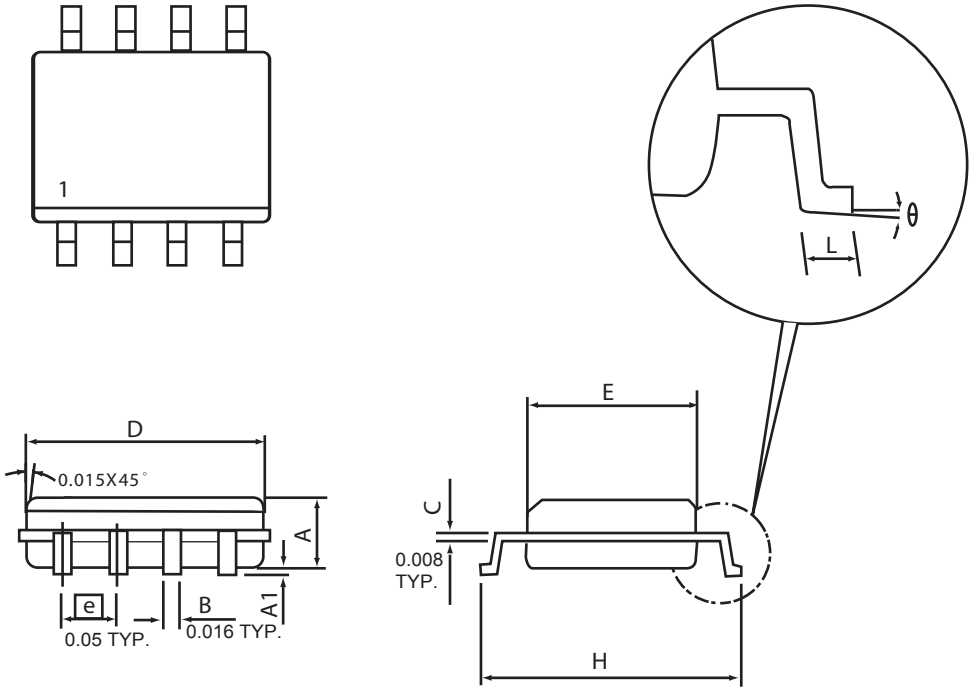
PACKAGE OUTLINE DIMENSIONS

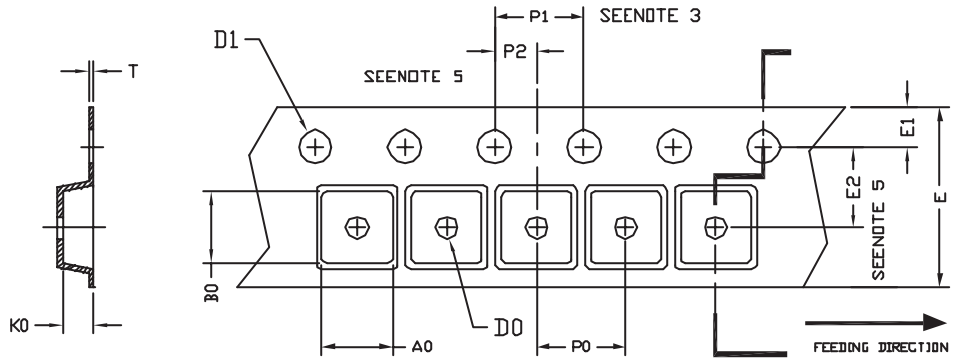
SO-8



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.35	1.75	0.053	0.069
A1	0.10	0.25	0.004	0.010
D	4.80	4.98	0.189	0.196
E	3.81	3.99	0.150	0.157
H	5.79	6.20	0.228	0.244
L	0.41	1.27	0.016	0.050
θ	0°	8°	0°	8°

SO-8 Tape and Reel Data

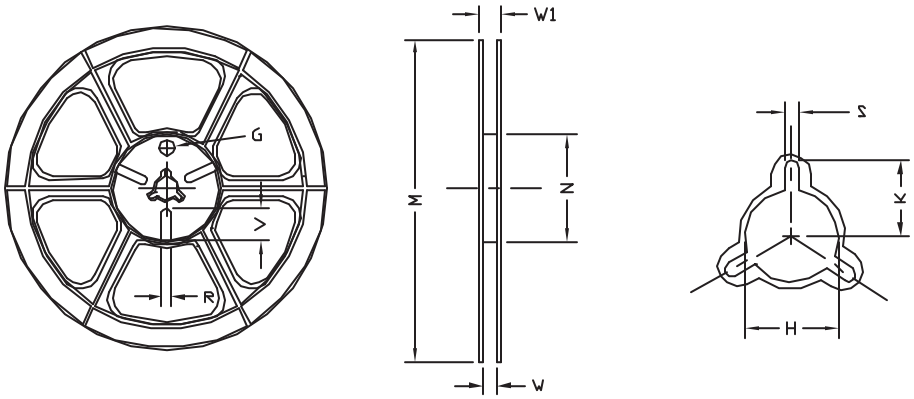
SO-8 Carrier Tape



unit:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
SOP 8N 150mil	6.40	5.20	2.10	ϕ1.5 (MIN)	ϕ1.5 + 0.1 - 0.0	12.0 ±0.3	1.75	5.5 ±0.05	8.0	4.0	2.0 ±0.05	0.3 ±0.05

SO-8 Reel



UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	W1	H	K	S	G	R	V
12 mm	ϕ330	330 ± 1	62 ±1.5	12.4 + 0.2	16.8 - 0.4	ϕ12.75 + 0.15	---	2.0 ±0.15	---	---	---